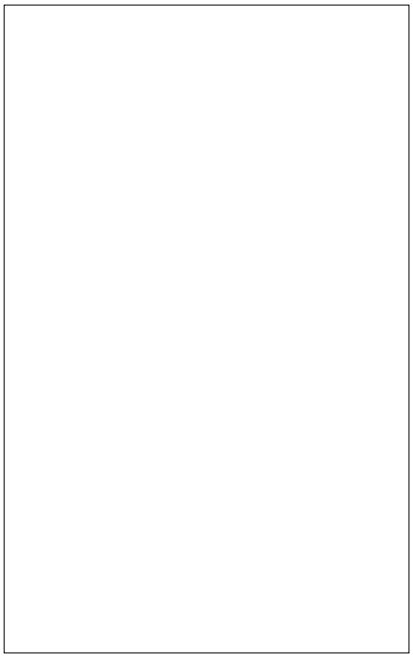
JCT1225C 25A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1225C SCR provides high dV/dt rate with strong resistance to electromagnetic interference.It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-220C is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	1200	V
I_{GT}	”40	mA

ABSOLUTE MAXIMUM RATINGS

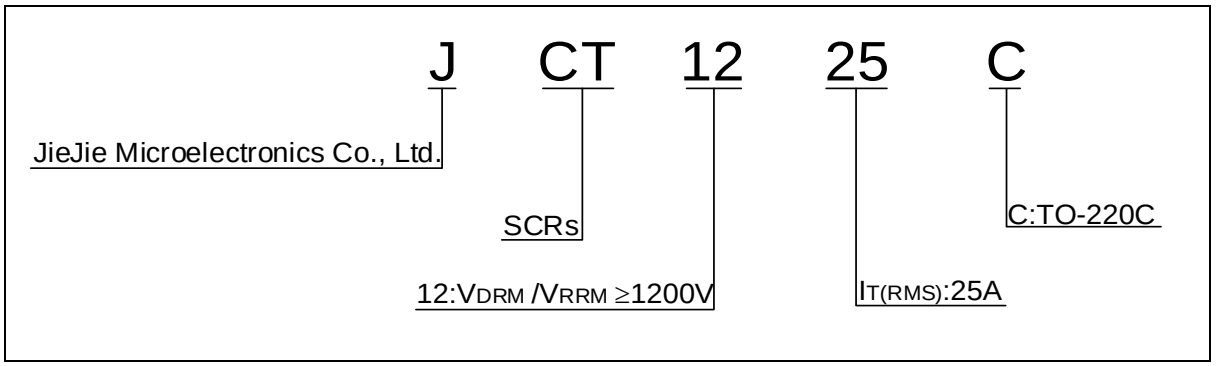
Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	1200	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	1200	V
Average on-state current (T_C 0 96)	$I_{T(AV)}$	16	A
RMS on-state current (T_C 096)	$I_{T(RMS)}$	25	A
Non repetitive surge peak on-state current (t_p=10ms, T_j=25)	I_{TSM}	320	A
Non repetitive surge peak on-state current (t_p=8.3ms, T_j=25)		352	
I^2t value for fusing (t_p=10ms , T_j=25)	I^2t	512	A^2s
Critical rate of rise of on-state current (I_G=2× I_{GT}, f=100Hz , T_j=125)	dI/dt	200	A s
Peak gate current (t_p=20 s , T_j=125)	I_{GM}	5	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W

Peak gate power	P_{GM}	20	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33	-	-	40	mA
V_{GT}		-	-	1	V
V_{GD}	V	-	-		

ORDERING INFORMATION



MARKING

FIG.1: Maximum power dissipation versus RMS on-state current

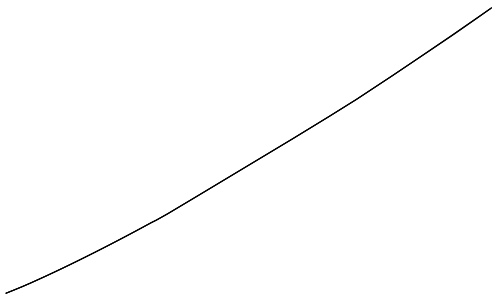


FIG.2: RMS on-state current versus case temperature

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